- LHC 14 TeV pp collider at CERN start summer 2008
- Gradual increase of luminosity up to  $L = 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$  in 2008-2011
- SLHC major increase of luminosity up to  $L = 10^{35} \text{ cm}^{-2} \text{ s}^{-1}$  in 2016-2017
- How can 3D electronics technology help us to challenge the physics at LHC ?



#### **Pixel Vertex Detector**





- ATLAS 80 millions pixels 50x400 µm
- CMS 66 millions pixels 100x150 μm

#### Pileup

$<\!\!N_{vrt}\!\!>$ - mean number of pileup vertices in $\pm 150 \mu m$ from primary vertex					Z <sub>vertex</sub> resolution for current ID is ≤50µm	
	$\sigma_{IR} = 5.6 \text{cm}$ $N_{int} = 23$	$\sigma_{IR} = 2.1 \text{cm}$ $N_{int} = 88$	$\sigma_{IR} = 2.1 \text{cm}$ $N_{int} = 176$	$\sigma_{IR} = 3.5 cm$ $N_{int} = 510$		
<n<sub>vrt&gt; at Z=0mm</n<sub>	0.05	0.49	0.99	1.7	1	
Z=20mm	0.05	0.31	0.63	1.4	8	

- LHC L =  $10^{34}$  cm<sup>-2</sup> s<sup>-1</sup> pixel occupancy 0.4 10<sup>-3</sup>
- SLHC L =  $10^{35}$  cm<sup>-2</sup> s<sup>-1</sup> with 50 ns bunch pixel occupancy 6.0  $10^{-3}$
- Wrong selection of primary vertex, admixture of pileup into jets
- Standard pile-up decrease b-tagging performance by ~20%
- Decrease of the pixel pitch size from 400 µm to 200 µm compensate b-tagging by ~20%

**ATLAS Pixel Front End size** 





#### **Importance of low mass**

- Decrease of the material in b-layer by 0.6% X0 improves b-tagging by 20%
- Many small gains to be investigated with 3D electronics solutions:
- Reduce power consumption->reduce cooling->reduce material
- Reduce overlaps: put end of column buffers on 3D tier-3
- Replace flex-hybrid and module controller by 3D tier-3
- Reduce power cables by DC-DC converters, serial powering. Could 3D help?
- Reduce usage of W and Cu:  $1\mu m W = 4\mu m Cu/Sn = 26\mu m Si/Al$



Buffers, builder digital analog sensor



Efficiency

- Loss of 3% of b-layer efficiency deteriorate b-tagging by 20%
- R&D on yield of 3D interconnections needed
- Stability of interconnections with multiple thermal cycling +- 30 degrees ?
- Radiation resistance up to 400 Mrad , ageing, corrosions ?
- Chip size and yields (wafer to wafer versus dice to wafer)



- Reduce significantly the cost by replacing bump-bonding ?
- Keep compatibility with different sensor options: planar Si,
  3D silicon, diamond ?
- Increase SEU tolerance by implementing triple registers in extra space with many Tiers
- Potentiality for track trigger option: local clustering, increased latency, fast readout etc

- CMS: interest for Fermilab 3D electronics R&D (see talk Ray Yarema)
- ATLAS: Bonn-Dortmund-Oslo-Interon-MPI\_Munich proposal for RD on 3D integration of sensors and electronics and on thin pixel sensors
- ATLAS: interest in Marseille-Orsay-Paris for the R&D on the 3D version of the FE-I4 pixel chip with 130 nm CMOS technology.

- Munich prototype module expected in 2009
- Thinned ATLAS FE-I3 chip bonded with SLID to thin 75  $\mu m$  Si sensor
- Via through FE-I3 for wire-bond pad



- 3D electronics offers the reduction of the pixel size needed at SLHC
- Feedback on the material reduction from 3D electronics should be investigated
- RD's for technology choice (SLID, Via (first/last) etc) are needed
- Qualifications for efficiency, yields, thermo cycling, radiation are needed
- Investigate if 3D interconnections could be less expensive than bump-

bonding for interconnections with different kind of sensors

• More unexpected benefits of 3D electronics for SLHC are quite probable

**Spares** 

**Space b-tagging** 

Efficiency of b-jet tagging  $\varepsilon_{b}$ 

**Rejection of light jets (udscg)**  $R_j = 1./\epsilon_i$ 



#### **Impact parameters**



## Layout Material budget

To reduce thickness of new layer:

- Old b-layer R=5.05 cm 2.2 % X0
- New b-layer R=3.7 cm 1.2 % X0



